Chu-Young Cho

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30 papers	1,735 citations	19 h-index	30 g-index
30 ext. papers	1,856 ext. citations	3.6 avg, IF	4 L-index

#	Paper	IF	Citations
30	Improved performance of InGaN/GaN Near-UV light-emitting diodes with staircase hole injector. *Engineering Research Express*, **2021**, 3, 015004	0.9	1
29	Enhanced Optical Output Power of Blue Light-Emitting Diode Grown on Sapphire Substrate with Patterned Distributed Bragg Reflector. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q66-Q69	2	3
28	White light emission of monolithic InGaN/GaN grown on morphology-controlled, nanostructured GaN templates. *Nanotechnology*, **2017**, 28, 225703	3.4	7
27	Enhanced optical output and reduction of the quantum-confined Stark effect in surface plasmon-enhanced green light-emitting diodes with gold nanoparticles. *Optics Express*, **2016**, 24, 7488-94	3.3	25
26	Improvement of optical and electrical properties of indium tin oxide layer of GaN-based light-emitting diode by surface plasmon in silver nanoparticles. *Thin Solid Films*, **2015**, 590, 76-79	2.2	6
25	Enhanced Internal Quantum Efficiency and Light Extraction Efficiency of Light-emitting Diodes with Air-gap Photonic Crystal Structure Formed by Tungsten Nano-mask. *Bulletin of the Korean Chemical Society*, **2014**, 35, 705-708	1.2	1
24	Surface plasmon enhanced light emission from AlGaN-based ultraviolet light-emitting diodes grown on Si (111). *Applied Physics Letters*, **2013**, 102, 211110	3.4	65
23	Near milliwatt power AlGaN-based ultraviolet light emitting diodes based on lateral epitaxial overgrowth of AlN on Si(111). *Applied Physics Letters*, **2013**, 102, 011106	3.4	41
22	Localized surface plasmon-enhanced near-ultraviolet emission from InGaN/GaN light-emitting diodes using silver and platinum nanoparticles. *Optics Express*, **2013**, 21, 3138-44	3.3	37
21	Near-ultraviolet light-emitting diodes with transparent conducting layer of gold-doped multi-layer graphene. *Journal of Applied Physics*, **2013**, 113, 113102	2.5	22
20	Enhanced Optical Power of InGaN/GaN Light-Emitting Diode by AlGaN Interlayer and Electron Blocking Layer. *IEEE Photonics Technology Letters*, **2012**, 24, 1991-1994	2.2	11
19	Au nanoparticle-decorated graphene electrodes for GaN-based optoelectronic devices. *Applied Physics Letters*, **2012**, 101, 031115	3.4	42
18	Enhanced Blue Emission from InGaN Quantum Wells by Surface Plasmon in Multi-Walled Carbon Nanotubes. *ECS Journal of Solid State Science and Technology*, **2012**, 1, R140-R142	2	
17	Enhanced optical output power of green light-emitting diodes by surface plasmon of gold nanoparticles. *Applied Physics Letters*, **2011**, 98, 051106	3.4	124
16	High-efficiency light-emitting diode with air voids embedded in lateral epitaxially overgrown GaN using a metal mask. *Optics Express*, **2011**, 19 Suppl 4, A943-8	3.3	34
15	Surface plasmon-enhanced light-emitting diodes with silver nanoparticles and SiO2 nano-disks embedded in p-GaN. *Applied Physics Letters*, **2011**, 99, 041107	3.4	56
14	Growth and Separation of High Quality GaN Epilayer from Sapphire Substrate by Lateral Epitaxial Overgrowth and Wet Chemical Etching. *Applied Physics Express*, **2011**, 4, 012104	2.4	18

13	Improvement of efficiency droop in InGaN/GaN multiple quantum well light-emitting diodes with trapezoidal wells. *Journal Physics D: Applied Physics*, **2010**, 43, 354004	3	37
12	Green Light-Emitting Diodes on Semipolar {1122} Microfacets Grown by Selective Area Epitaxy. *Journal of the Electrochemical Society*, **2010**, 157, H86	3.9	6
11	Enhanced light extraction in light-emitting diodes with photonic crystal structure selectively grown on p-GaN. *Applied Physics Letters*, **2010**, 96, 181110	3.4	19
10	Surface plasmon-enhanced light-emitting diodes using silver nanoparticles embedded in p-GaN. *Nanotechnology*, **2010**, 21, 205201	3.4	72
9	Improvement of light output power of InGaN/GaN light-emitting diode by lateral epitaxial overgrowth using pyramidal-shaped SiO(2). *Optics Express*, **2010**, 18, 1462-8	3.3	25
8	Large-scale patterned multi-layer graphene films as transparent conducting electrodes for GaN light-emitting diodes. *Nanotechnology*, **2010**, 21, 175201	3.4	233
7	Effect of Mg doping in the barrier of InGaN/GaN multiple quantum well on optical power of light-emitting diodes. *Applied Physics Letters*, **2010**, 96, 051113	3.4	55
6	Effect of electron blocking layer on efficiency droop in InGaN/GaN multiple quantum well light-emitting diodes. *Applied Physics Letters*, **2009**, 94, 231123	3.4	244
5	Effect of InGaN quantum dot size on the recombination process in light-emitting diodes. *Applied Physics Letters*, **2008**, 92, 253105	3.4	41
4	InGaN□GaN multiple quantum wells grown on microfacets for white-light generation. *Applied Physics Letters*, **2008**, 93, 241109	3.4	35
3	Phosphor-free white light-emitting diode with laterally distributed multiple quantum wells. *Applied Physics Letters*, **2008**, 92, 091110	3.4	53
2	Enhanced light extraction efficiency in flip-chip GaN light-emitting diodes with diffuse Ag reflector on nanotextured indium-tin oxide. *Applied Physics Letters*, **2008**, 93, 021121	3.4	14
1	Surface-Plasmon-Enhanced Light-Emitting Diodes. *Advanced Materials*, **2008**, 20, 1253-1257	24	408